# 英飞凌驱动芯片产品介绍





### IPC Gate Driver Product Types Portfolio Segmentation





### New PL67 Gate Driver product segmentation – HA+ Multiple Consumer and Industrial applications to 10 kW





icts **BOLD** = Today's focus

### 1ED44175N01B / 1ED44173N01B advantages

Cost effective, space saving, accurate, and fast time-to-market PFC solutions





#### \* - example circuit with 1ED44175N01



PN	6EDL04N02	<u>6ED003L02-</u> <u>F2</u>	<u>IRS2008</u> *	<u>IRS2007</u> *	<u>IRS2005</u> *	<u>IRS2011</u>	<u>IR2011</u>	<u>IR2010</u>
Voltage Class	200 V	200 V	200 V	200 V	200 V	200 V	200 V	200 V
Technology	SOI	SOI	JI	JI	II	JI	JI	JI
Configuration	3-phase	3-phase	НВ	НВ	HSLS	HSLS	HSLS	HSLS
lo+/- typ.	0.165 / 0.375 A	0.165 / 0.375 A	0.29 / 0.6 A	0.29 / 0.6 A	0.29 / 0.6 A	1/1A	1/1A	3/3A
UVLO (on/off) typ.	9 V / 8.1 V	11.7 / 9.8 V	8.9 / 8.2 V	8.9 / 8.2 V	8.9 / 8.2 V	9.0 / 8.2 V	9.0 / 8.2 V	8.6 / 8.2 V
Propagation delay (on/off) typ.	530 / 530 ns	530 / 490 ns	680 / 150 ns	160 / 150 ns	160 / 150 ns	60 / 60 ns	80 / 75 ns	95 / 65 ns
Deadtime typ.	310 ns	310 ns	520 ns	520 ns				
Features	Integrated bootstrap diode		Cost effective					
Package Options	TSSOP-28	Contineon	DSO-8, 4x4 MLPO	2-14		DSO-8, PDIP8		DSO-16 wide body, PDIP14

\*IRS2004, IRS2003, and IRS2001 are not recommended for new designs. For new designs we recommend IRS2008, IRS2007, and IRS2005

# IRS2005, IRS2007, and IRS2008 at a glance 200 V high & low side and half bridge drivers



#### Key Features

- 200 V gate driver family tailored for low voltage (24 V, 36 V, and 48 V) and mid voltage (60 V, 80 V and 100 V) motor drive applications
- Maximum offset voltage 225 V
- > 290 mA / 600 mA typical source/sink current
- > 10 V to 20 V gate drive supply range
- > 3.3 V, 5 V, and 15 V logic compatible
- > 8.9 / 8.2 V under-voltage lockout protection
- > Interlocked (IRS2007, IRS2008)
- > Floating channel designed for bootstrap operation
- Logic operational for VS of -8 V
- Tolerant to negative transient voltage, dV/dt immune
- Matched propagation delays
- Shutdown input turns off both channels (IRS2008)

Part Number	Config.	Prop. Delay ton/off typ. (ns)	Deadtime typ. (ns)	Control Inputs	Package	
IRS2008	HB	680/150	520	IN, SD	DSO-8,	
IRS2007	HB	160/150	520	HIN, /LIN	MLPQ-14	
IRS2005	HS+LS	160/150		HIN, LIN		

\*IRS2001 is not recommended for new designs, IRS2005 replaces IRS2001. IRS2008 can replace IRS2004. IRS2007 can replace IRS2003.



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**Infineon Proprietary** 

# Infineon Silicon-On-Insulator (SOI) technology Solution advantages





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# Infineon 650 V SOI half-bridge and high and low side level-shift gate driver family





#### 2ED2106/8/9—New 650 V, 0.7 A driver family 2ED2181/2/3/4—New 650 V, 2.5 A driver family

- Integrated bootstrap diode (BSD)
- > Tolerant to negative transient voltage up to 100 V
- > Reduced level shift losses for switching frequencies above 100 kHz
- > Superior latch-up immunity with SOI
- > For 650 V IGBT and MOSFET

#### 2ED2106/8/9 & 2ED2181/2/3/4 - Released

- 200 ns propagation delay, HB & HS+LS, DSO-8/-14
- Air-Con fans/ Fridge / Motor Drive

#### 2ED2101/3/4 & 2ED2110 – Fast Level Shift Family

- **100 ns** propagation delay, HB & HS+LS, DSO-8/-16
- Lighting / SMPS / Motor Drive

### EiceDRIVER™ 1ED Compact (1ED-AF/1ED-MF)

Single-channel isolated driver with active Miller clamp or separate output in DSO-8 150 mil

#### **Key Features**

- > Single channel isolated gate driver with up to 10 A (no booster required)
- > Active Miller Clamp or Separate outputs
- Galvanic functional isolation voltages up to 1200 V
- 40 V absolute maximum output supply voltage (1ED-AF) for Bipolar power supply preventing inadvertent dV/dt turn-on
- > Exceptional CMTI robustness > 100 kV/µs
- > Low propagation delay of **300 ns** or **125 ns**, suitable for fast switching application

**Typical Applications** 

**EV charger** 

- DSO-8 150 mil (4mm creepage)
- → For high voltage IGBT, MOSFET, CoolSiC<sup>™</sup> SiC MOSFET
- > Evaluation board available:
  - > EVAL-1EDI60I12AF
  - > EVAL-PS-E1BF12-SIC
  - > EVAL\_HB\_PARALLELGAN
  - > EVAL\_800W\_PSU\_3P\_P7



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#### SGND

+5 V

Separate sink/source outputs

VCC1

100n



Sample schematic

OUT

+15 V

<u>— 1</u>и

	DSO-8 150 mil	1EDI60N12AF	1EDI60I12AF	1EDI20N12AF	1EDI30I12MF
ED-C	Typ. Output current	±10 A	±10 A	±4 A	±6 A
Compact	Propagation delay	125 ns	300 ns	125 ns	300 ns
	Input Filter	40 ns	240 ns	40 ns	240 ns
ompact	CMTI	100 kV/µs	100 kV/µs	100 kV/µs	100 kV/µs
	Output supply voltage	40 V	40 V	40 V	20 V
Aircon	Propagation delay matching	20 ns	20 ns	20 ns	20 ns
	UVLO (on)	9 V	12 V	9 V	12 V

IGBI

+SiC

### EiceDRIVER™ X3 Compact (1ED31xx) family

Single-channel isolated gate driver with active Miller clamp or separate output



#### Product highlights

- Single channel isolated gate driver with **5.5 / 10 / 14 A** (no booster required)
- > Galvanic functional isolation voltages up to 2300 V
- > 90 ns propagation delay with 30 ns input filter, 7 ns propagation delay matching
- > Active Miller Clamp or Separate outputs
- > Exceptional CMTI robustness > 200 kV/µs
- > 40 V absolute maximum output supply voltage
- > Isolation capabilities & certification
  - > 1ED31xxMU12F: UL 1577 certified V<sub>ISO</sub>=3 kV(rms)
  - > 1ED31xxMU12H: UL 1577 certified V<sub>Iso</sub>=5.7 kV(rms)
  - → 1ED31xxMC12H: UL 1577 & VDE 0884-11 certified V<sub>IORM</sub>=1767 V (planned)
- > DSO-8 150 mil (4 mm creepage) & 300 mil package (8 mm creepage)
- > Evaluation board available:



> EVAL-1ED3121MX12H; EVAL-1ED3122MX12H; EVAL-1ED3124MX12H

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Sample schematic

DSO-8 150 mil		1ED3124MU12F		1ED3125MU12F
		1ED3123MU12H	1ED3120MU12H	
DSC-0 300 mil	1ED3131MU12H	1ED3124MU12H	1ED3121MU12H	1ED3122MU12H
Typ. Output current	±5.5 A	±14 A	±5.5 A	±10 A
Propagation delay	280 ns	90 ns	90 ns	90 ns
Input Filter	180 ns	30 ns	30 ns	30 ns
CMTI	200 kV/µs	200 kV/µs	200 kV/µs	200 kV/µs
Output supply voltage	40 V	40 V	40 V	40 V
Propagation delay matching	7 ns	7 ns	7 ns	7 ns
UVLO (on)	12 V	10 V or 12 V	10 V or 12 V	10 V or 12 V 🛖

Typical Applications



Lighting

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### EiceDRIVER™ Enhanced 1ED-F2/B2/FT/BT family

infineon

### Single-channel isolated gate driver with active Miller clamp and DESAT

#### Key Features

#### Sample Schematic

- Single channel isolated gate driver IC for IGBT and SiC MOSFET
- > Galvanic isolation with coreless transformer up to 1200 V
- > 2 A typical rail-to-rail output current
- > Exceptional CMTI robustness > 100 kV/µs
- > DESAT, Miller clamp, Short circuit clamping, Active shut-down, FLT & RDY
- > 195/190 ns Max. propagation delay (1ED-F2/B2)
- > **Two level turn off**, 2 µs Max. propagation delay (1ED-BT/FT only)
- > 28 V absolute maximum output supply voltage
- > 1ED-B2/BT Isolation capabilities & certification:
  - UL 1577 with V<sub>ISO</sub> = 3750 V (rms) for 1 min
  - VDE 0884-10 for V<sub>IORM</sub>=1420 V, V<sub>IOTM</sub>=6000 V (standard expired, while testing methodology remain unchanged)
- DSO-16 300 mil wide body package with 8 mm creepage www.Infineon.com/gdenhanced





#### **Value Proposition**

- > Immunity against negative transient voltages, no latch up
- > Optimal controllability of application with dedicated UVLO
- > Reduced external components enables simple PCB layout and faster design-in
- Evaluation board available:
  - EVAL-1ED020I12-B2
  - EVAL-1ED020I12-BT
  - 2ED250E12-F
  - 6ED100E12-F2
  - 2ED100E12-F2



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### EiceDRIVER™ Enhanced 2ED020I12-F2 (2ED-F2)

Dual-channel isolated gate driver with active Miller clamp and DESAT



#### Key Features

- > Dual channel isolated gate driver IC for IGBT and SiC MOSFET
- > Galvanic isolation with coreless transformer up to 1200 V
- > 2 A typical rail-to-rail output current
- > 170 ns / 165 ns propagation delay
- > Exceptional CMTI robustness > 50 kV/µs
- > DESAT, Miller clamp, Short circuit clamping, Active shut-down, FLT & RDY
- > 28 V absolute maximum output supply voltage
- > 11 V / 12 V under-voltage lockout
- > Small footprint in DSO-36 300 mil package with 8 mm creepage
- > Evaluation board available:
  - EVAL-2ED020I12-F2



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# EV charger Solar Image: Ima



#### Value Proposition

- Galvanic Insulation
- Integrated protection features such as DESAT and active Miller clamp
- > Suitable for operation at high ambient temperature



#### Sample Schematic

### EiceDRIVER™ Enhanced 2ED020I12-FI & 2ED020I06-FI (2ED-FI)



Half-bridge isolated gate driver (isolated only on high side)

#### **Key Features**

- Galvanic isolation based on coreless transformer on the high side, half bridge isolated gate driver IC
- > Drive up to 1200 V IGBT and n channel power MOSFET (2ED020I12-FI)
- > Interlock (shoot through protection)
- > Power supply operating range from **14 V** to **18 V**
- > Gate drive currents of +1 A / -2 A
- > Dedicated Shutdown input
- Matched propagation delay for both channels (typ. 85ns propagation delay / ±25ns propagation delay mismatch)
- > High dV/dt immunity
- > Low power consumption
- > General purpose operational amplifier
- > General purpose comparator
- > For High Power Constant Current Power Supply
- > 600 V version also available: 2ED020I06-FI

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#### Value Proposition

- > Best cost performance ratio product in EiceDRIVER™ Enhanced family
- General purpose operational amplifier and the comparator for current measurement and OCP reduce system cost by up to 0.15€ per half bridge
- Reduced external components enables a simpler PCB layout, faster designin, and improved reliability





### 6ED2230S12T 3-Phase, 1200V SOI Gate Driver

#### **Key Features**

- > 6ED2230S12T (1200 V Infineon SOI Technology)
- > Integrated, Ultra fast, low R<sub>DSON</sub> bootstrap diode
- > Integrated 360ns dead-time
- > Output current: I<sub>0+</sub> 350mA, I<sub>0-</sub> 650mA
- > Independent Under-voltage lockout for  $V_{CC}$  and  $V_{BS}$
- > 25 V V<sub>cc</sub> maximum voltage supply
- > 3.3V, 5V, 15V input logic compatible
- Best in class minus VS performance
  - > -100 V with repetitive 700 ns pulses
- > SOIC-28 package (with 4 pins removed for high clearance)
- > Over current protection (ITRIP +/-5% reference)
- > Less than 1 us output shutdown for OCP events
- > Fault reporting, automatic Fault clear and Enable function on the same pin (RFE)
- > 2kV HBM ESD

I <sub>O+/-</sub> (typ) [mA]	Ton/off (typ) [ns]	DT (typ) [ns]	Tr/f (typ) [ns]	Input Filter (Typ) (ns)	Vcc/Vbs UVLO typ.
350/650	600	360	40	300	10.4-11.4 / 9.4-10.4

#### **Typical Applications**



#### **Sample Schematic**



#### **Performance and Value**

- > Integrated, fast, and low R<sub>DSON</sub> Bootstrap Diode
- Simplified lower-cost driver for 1200V IGBTs
- > Industry leading minus VS robustness
- Increased reliability and noise immunity
- > Over-current protection with +/-5% reference
- > Independent UVLO for  $V_{CC}$  and  $V_{BS}$
- > Matched propagation delay
- Easy to use for fast time to market



### Infineon gate driver success story Induction heating (IH) multi-stove oven





- > Application: IH multi-stove oven (3.5 kW)
- > **Customer**: world-wide home appliance customer
- Products:
  - Gate Driver: 2ED21824S06J
    - 650 V, 2.5 A, half bridge driver
  - Switch: IKW50N60H3
- **Competition**: Toshiba + AOS
- > WHY we are successful:
  - Infineon's advantage when fighting with Optocoupler solution;
    - Longer lifetime & reliability
    - Accurate current sensing and sampling, smaller  $t_{\text{ON}}$  /  $t_{\text{OFF}}$  .
  - Total solution with Driver + IGBTs.
  - System know-how and direct engagement.

### Infineon gate driver success story Residential air conditioners (RAC)





- > Application: Boost-PFC in residential aircon
- Customer: World-wide market-leaders for residential air conditioners in China and India with MPs from CY20Q4
- > Product:
  - Gate Driver: 1ED44175N01B
    - 25 V, 2.6 A, single low side driver with OCP
  - Switch:
    - PFC IGBT: e.g. TRENCHSTOP<sup>™</sup> 5 IGBT
    - PFC Diode: e.g. RAPID<sup>™</sup> 1 Diode
    - Controller & CIPOS™ IPM: e.g. IM564-X6D
- WHY we are successful:
  - Cost effective and space saving
    - NEW 2.6 A 1-ch low-side driver with integrated OCP, fault, and enable
  - Fits perfectly with CIPOS™ IPM with PFC
  - Strong technical support and know-how of low-side gate drive circuits from 20 years of experience
  - Excellent business continuity support for sudden high volume ramp-up

### Infineon gate driver success story 200 W compressor inverter for refrigerators





- Application: 200 W motor control inverter for linear compressor
- **Customer**: world-wide refrigerator compressor market-leader (Americas)
- Products:
  - Gate Driver: 2ED2304S06F derivative
    - 650 V, 0.7 A, half bridge driver
  - Switch: IGBT
- WHY we are successful:
  - Infineon SOI technology
  - Reduced Level shift losses for higher efficiency
  - Integrated Boot Strap Diode for reduce size / BOM cost
  - High negative VS rating for improved reliability / robustness
  - Integrated, advanced input filter for stable operation
  - Technical workshops, application support, fast turn-around



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